# N - Channel 30 V (D-S) MOSFET

PRODUCT SUMMARY					
V <sub>DS</sub> (V)	R <sub>DS(on)</sub> (mΩ)(Typ.)	I <sub>D</sub> (A) <sup>a</sup>	Q <sub>g</sub> (Typ.)		
30	1.8 at V <sub>GS</sub> = 10 V	58	37.5 nC		
30	2.7 at V <sub>GS</sub> = 4.5 V	56	37.3110		

#### **FEATURES**

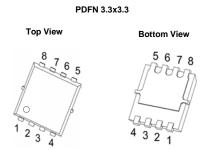
- DT-Trench MOSFET
- 100 %  $\rm R_{\rm g}$  and UIS Tested
- Low RDS(ON)
- · High Current Capability

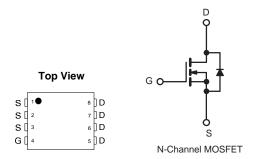


ROHS

#### **APPLICATIONS**

- · Battery charging and discharging for battery pack
- · Power switch for Adaptor/ Charger





<b>ABSOLUTE MAXIMUM RATINGS</b> (T <sub>C</sub> = 25 °C, unless otherwise noted)					
PARAMETER	SYMBOL	LIMIT	UNIT		
Drain-Source Voltage	V <sub>DS</sub>	30	V		
Gate-Source Voltage	V <sub>GS</sub>	± 20	V		
Continuous Drain Current (T, = 175 °C) <sup>a</sup>	T <sub>C</sub> = 25 °C		58	А	
Continuous Drain Current (1) = 175 C)	T <sub>C</sub> = 100 °C	I <sub>D</sub>	41		
Pulsed Drain Current <sup>b</sup>	I <sub>DM</sub>	230			
Single Avalanche Energy	E <sub>AS</sub>	150	mJ		
Maximum Power Dissipation <sup>c</sup>	T <sub>C</sub> = 25 °C	P <sub>D</sub>	83	W	
Maximum Fower Dissipation	T <sub>C</sub> = 100 °C	PD PD	41.6	VV	
Operating Junction and Storage Temperature F	T <sub>J</sub> , T <sub>stg</sub>	- 55 to +175	°C		

THERMAL RESISTANCE RATINGS					
PARAMETER	SYMBOL	LIMIT	UNIT		
Junction-to-Ambient (PCB Mount) <sup>d</sup>	R <sub>thJA</sub>	55	°C/W		
Junction-to-Case (Drain)	R <sub>thJC</sub>	1.8	- C/vv		

#### Notes

- a. Calculated continuous current based on maximum allowablejunction temperature.
- b. Repetitive rating; pulse width limited by max. junction temperature.
- c. Pd is based on max. junction temperature, using junction-case thermal resistance.
- d. The value of R<sub>BJA</sub> is measured with the device mounted on 1 in 2 FR-4 board with 2oz. Copper,in a still air environment with Ta=25 °C.





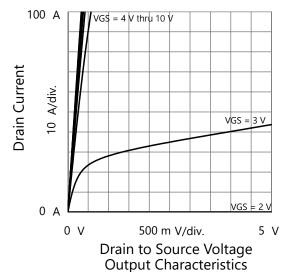
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT	
Static				•			
Drain-Source Breakdown Voltage	V <sub>DS</sub>	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	30	-	-	V	
Gate Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}, I_D = 250 \mu A$	1.0	-	3.0	v	
Gate-Body Leakage	I <sub>GSS</sub>	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$	=	-	± 100	nA	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	$V_{DS} = 30 \text{ V}, V_{GS} = 0 \text{ V}$	-	-	1	1 10 μΑ	
zero Gate Voltage Drain Current		V <sub>DS</sub> = 24 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 55 °C	=	-	10		
On-State Drain Current <sup>a</sup>	n-State Drain Current <sup>a</sup> $I_{D(on)}$ $V_{DS} \ge 5 \text{ V}, V_{GS} = 5 \text{ V}$		58	-	-	Α	
Drain-Source On-State Resistance a	D	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 10 A	-	1.8	2.5		
Dialii-Source Oil-State nesistance "	R <sub>DS(on)</sub>	V <sub>GS</sub> = 4.5 V, I <sub>D</sub> = 8 A	-	2.7	3.8	mΩ	
Forward Transconductance <sup>a</sup>	9 <sub>fs</sub>	V <sub>DS</sub> = 5 V, I <sub>D</sub> = 10 A	-	95	-	S	
Dynamic <sup>b</sup>				•			
Input Capacitance	C <sub>iss</sub>		-	2150	-		
Output Capacitance	C <sub>oss</sub>	V <sub>GS</sub> = 0 V, V <sub>DS</sub> = 15 V, f = 1 MHz	-	937	-	pF	
Reverse Transfer Capacitance	C <sub>rss</sub>		-	66	-		
Total Gate Charge <sup>c</sup>	Qg		-	37.5	-		
Gate-Source Charge <sup>c</sup>	$Q_{gs}$	$V_{DS} = 15 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 10 \text{ A}$	-	4	-	nC	
Gate-Drain Charge <sup>c</sup>	Q <sub>gd</sub>		-	6	-		
Gate Resistance	$R_g$	f = 1 MHz	-	2.9	-	Ω	
Turn-On Delay Time <sup>c</sup>	t <sub>d(on)</sub>		-	11	-		
Rise Time <sup>c</sup>	t <sub>r</sub>	$V_{DS} = 15 \text{ V}, I_{D} = 10 \text{ A}, R_g = 2.5 \Omega$	-	10	-		
Turn-Off Delay Time <sup>c</sup>	t <sub>d(off)</sub>	V <sub>GS</sub> = 10 V	-	100	-	ns	
Fall Time <sup>c</sup>	t <sub>f</sub>		-	25	-		
Drain-Source Body Diode Ratings and	Characterist	tics <sup>b</sup> (T <sub>C</sub> = 25 °C)					
Continuous Source-Drain Diode Current	I <sub>S</sub>	T <sub>C</sub> = 25 °C	-	-	58	А	
Pulsed Current (t = 100 μs)	I <sub>SM</sub>		-	-	230	Α	
Forward Voltage <sup>a</sup>	$V_{SD}$	I <sub>F</sub> = 1 A, V <sub>GS</sub> = 0 V	-	-	1.2	V	
Reverse Recovery Time	t <sub>rr</sub>	L = 10 A di/dt = 100 A/::5	-	13	-	ns	
Reverse Recovery Charge	$Q_{rr}$	I <sub>F</sub> = 10 A, di/dt = 100 A/μs		25	-	nC	

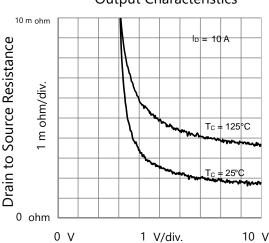
#### Notes

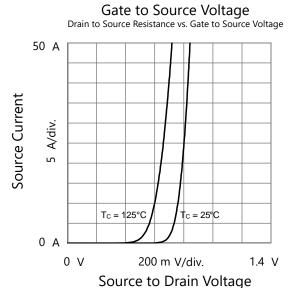
- a. Pulse test; pulse width  $\leq 300~\mu s,$  duty cycle  $\leq 2~\%.$
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

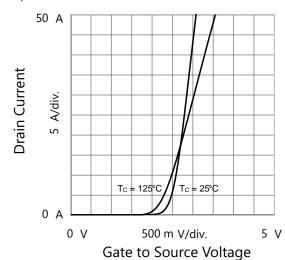
## TYPICAL CHARACTERISTICS (25°C, unless otherwise noted)

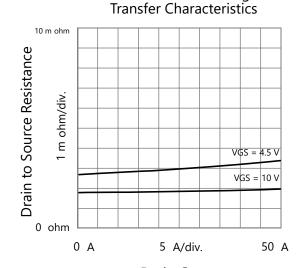


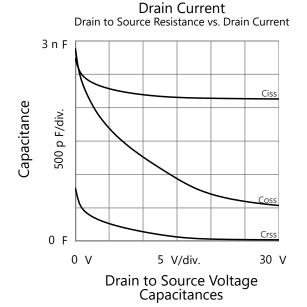




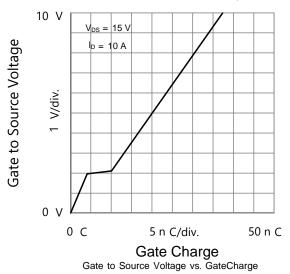
**Body Diode Forward Characteristics** 

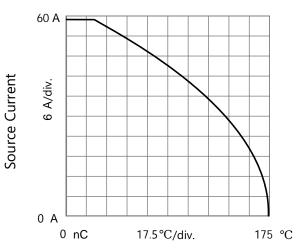




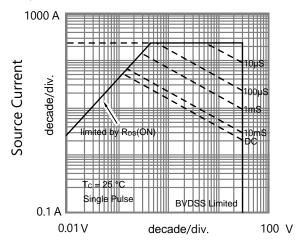


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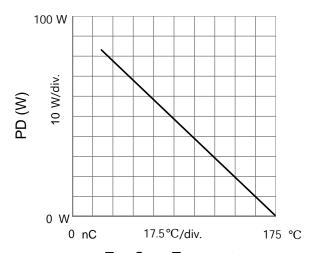




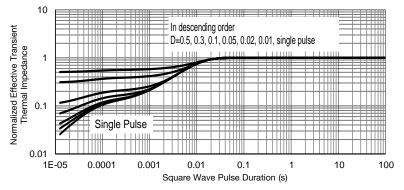
T<sub>C</sub> - Case Temperature
Current Derating



Source to Drain Voltage
Safe Operating Area, Junction-to-Ambient



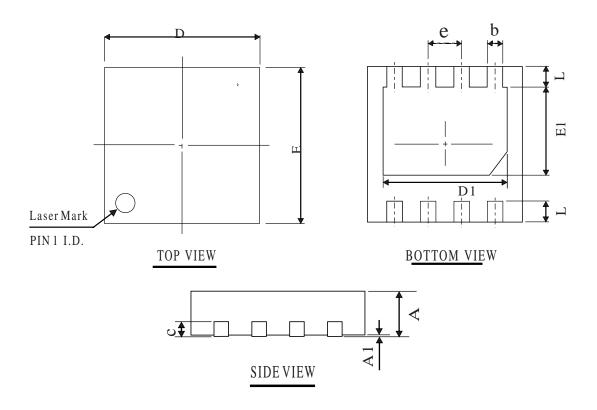
 $T_{C} \textbf{- Case Temperature}_{\text{Power Derating}}$ 



Normalized Thermal Transient Impedance, Junction-to-Case



# DFN3\*3-8L PACKAGE OUTLINE



# COMMON DIMENSIONS (UNITS OF MEASURE=mm)

SYMBOL	MIN	NOM	MAX
A	0. 60	0.75	0. 90
A1	0. 00	0.02	0. 08
b	0. 20	0.30	0.45
D	2. 85	3.00	3. 15
Е	2. 85	3.00	3. 15
D1	2. 10	2.40	2.70
E1	1.50	1.70	2.00
L	0. 20	0.40	0.60
С	0. 203 REF		
e	0. 65 BSC		

## OTHER DIMENSIONS

A	0. 50	0.55	0.60
A	0.40	0.45	0.50





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